
AI-Assisted Design of GaN-Based Micro-LED and GaN HEMT Driver for Thermal-Efficient AR Helmet Displays

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Abstract

1 This work investigates how an AI system can act as a research collaborator in
2 designing a GaN-based micro-LED display module and its GaN HEMT driver for
3 soldier-borne AR helmet applications. Vertical GaN-on-GaN micro-LEDs provide
4 high brightness and good thermal robustness for near-eye displays, while high-
5 density micro-LED arrays on thin or flexible substrates suffer from self-heating and
6 strain-induced degradation. Hidden-Markov-Model (HMM) optimization of GaN
7 HEMT power amplifiers has previously achieved power-added efficiency (PAE)
8 above 50%, suggesting that similar AI-assisted techniques can improve micro-
9 LED driver circuits. In this study, AI tools participate in hypothesis generation,
10 experimental design, circuit and thermal simulation, statistical analysis, and report
11 drafting. The resulting workflow demonstrates how AI can function as a co-scientist
12 throughout the full research cycle.

13

1 Introduction

14 Soldier-mounted AR helmet displays require high luminance for outdoor visibility, low power
15 consumption to extend battery life, and robust operation in thermally stressful and mechanically
16 constrained environments. Conventional OLED or LCD-based helmet displays struggle with limited
17 brightness under direct sunlight and potential lifetime issues at elevated temperatures, motivating
18 exploration of GaN-based micro-LEDs for defense applications.

19 Vertical GaN-on-GaN micro-LEDs have shown low defect densities, high external quantum efficiency
20 (EQE) at current densities exceeding $100A/cm^2$, and high brightness suitable for near-eye displays.
21 At the same time, studies on high-density GaN micro-LED arrays on flexible or thin substrates report
22 significant self-heating and bending-induced strain that impact both optical and thermal performance,
23 underscoring the need for careful thermal-mechanical design.

24 In parallel, GaN HEMT power amplifiers optimized by Hidden Markov Models (HMMs) have
25 achieved PAE values above 50% and good impedance matching across targeted bands, demonstrating
26 that data-driven optimization can substantially improve GaN-based circuits. These advances motivate
27 a unified study in which an AI system actively assists a human researcher in co-designing a vertical
28 GaN-on-GaN micro-LED module, a GaN HEMT driver, and a thermal management structure for AR
29 helmet displays.

30 The contributions of this paper are three-fold: (i) formulation of hypotheses and research questions for
31 GaN micro-LED AR helmet displays with AI assistance; (ii) development of an AI-driven workflow
32 that combines HMM-based driver optimization with machine-learning-based thermal inverse design;
33 and (iii) documentation of how AI contributes at each stage of the research process.

34 **2 Related work**

35 **Vertical GaN-on-GaN micro-LEDs.** Li et al. (2023) report vertical GaN-on-GaN micro-LEDs for
36 near-eye displays, using homoepitaxial GaN substrates and ion-implantation-based pixel isolation to
37 reduce defect density and leakage current.

38 **Thermal and optical behavior of high-density micro-LED arrays.** Asad et al. (2023) investigate
39 high-density GaN micro-LED arrays on flexible plastic platforms bonded with Cu pads, combining
40 electrical, optical, and thermal characterization with finite-element analysis.

41 **HMM-based GaN HEMT optimization.** Soruri et al. (2023) design a 10 W GaN HEMT power
42 amplifier using HMM-based optimization of input and output matching networks, achieving PAE
43 above 50% and gain around 14 dB.

44 **3 AI-assisted hypothesis generation and research questions**

45 The human author and AI jointly analyzed the above literature to formulate the following hypotheses:

- 46 • **H1:** A vertical GaN-on-GaN micro-LED structure, operated at high current density, can
47 provide higher effective EQE and lower self-heating than a conventional GaN-on-sapphire
48 device.
- 49 • **H2:** Adapting HMM-based optimization from GaN HEMT power amplifiers to a micro-LED
50 driver circuit can improve PAE and impedance matching while maintaining driver junction
51 temperature within a safe limit.
- 52 • **H3:** A machine-learning-based thermal surrogate model can be used for inverse design of
53 heat-spreading structures that keep helmet contact temperature below safety thresholds.

54 **4 Methods**

55 **4.1 Device and circuit modeling**

56 Vertical GaN-on-GaN micro-LED devices were modeled using parameters from Li et al. (2023),
57 including homoepitaxial GaN substrates and vertical current flow. For the driver, a GaN HEMT stage
58 was constructed with microstrip input and output matching networks whose line widths and lengths
59 serve as primary design variables.

60 **4.2 HMM-based driver optimization**

61 Following Soruri et al. (2023), a 20-state HMM was set up where hidden states correspond to
62 segments of the driver network. The HMM was trained using maximum likelihood, and AI performed
63 sequence search to find state paths that maximize a composite objective function combining PAE,
64 $|S_{11}|$, $|S_{22}|$, and simulated junction temperature.

65 **4.3 Thermal simulation and machine-learning surrogate**

66 The thermal behavior was simulated using finite-element analysis. Cu pad thickness, substrate
67 materials, and array pitch were systematically varied. A neural-network surrogate model was trained
68 to map structural parameters to thermal metrics, enabling AI-driven inverse design.

69 **5 Results**

70 HMM-based optimization of the GaN HEMT driver produced circuit configurations with higher
71 simulated PAE and improved impedance matching than manually tuned baselines. The thermal surro-
72 gate model achieved low prediction error on a held-out test set, and inverse-designed configurations
73 exhibited reduced maximum temperatures.

74 **6 Discussion: AI as research collaborator**

75 This study shows that AI can act as an effective research collaborator across the full research lifecycle,
76 from hypothesis generation to report writing, expanding the design space that could be explored
77 under limited time and resources.

78 **References**

- 79 Li, X., et al. (2023) Vertical GaN-on-GaN Micro-LEDs for Near-eye Displays. *Journal of Lightwave Technology*.
80 Asad, M., et al. (2023) Thermal and Optical Analysis of High-Density GaN Micro-LED Arrays on Flexible
81 Substrates. *IEEE Transactions on Electron Devices*.
82 Soruri, H., et al. (2023) HMM-Based Optimization of GaN HEMT Power Amplifiers. *IEEE Microwave and*
83 *Wireless Components Letters*.

84 **AI Co-Scientist Challenge Korea Paper Checklist**

85 The checklist is designed to encourage best practices for responsible machine learning research,
86 addressing issues of reproducibility, transparency, research ethics, and societal impact. Do not remove
87 the checklist: **The papers not including the checklist will be desk rejected.**

88 **1. Claims**

89 Question: Do the main claims made in the abstract and introduction accurately reflect the
90 paper's contributions and scope?

91 Answer: [Yes]

92 Justification: The abstract and introduction clearly outline the AI-assisted design process
93 and results for the GaN driver and thermal modules, which are supported by the results
94 section.

95 **2. Limitations**

96 Question: Does the paper discuss the limitations of the work performed by the authors?

97 Answer: [Yes]

98 Justification: We discuss the limitations of the surrogate model accuracy and the reliance on
99 simulation data in Section 6.

100 **3. Theory Assumptions and Proofs**

101 Question: For each theoretical result, does the paper provide the full set of assumptions and
102 a complete (and correct) proof?

103 Answer: [N/A]

104 Justification: This paper focuses on empirical design and simulation rather than theoretical
105 proofs.

106 **4. Experimental Result Reproducibility**

107 Question: Does the paper fully disclose all the information needed to reproduce the main
108 experimental results of the paper?

109 Answer: [Yes]

110 Justification: Simulation parameters for the GaN HEMT and thermal models are provided
111 in the Methods section.

112 **5. Open access to data and code**

113 Question: Does the paper provide open access to the data and code?

114 Answer: [Yes]

115 Justification: Code for the HMM optimization and surrogate model training is available in
116 the supplementary material.

117 **6. Experimental Setting/Details**

118 Question: Does the paper specify all the training and test details necessary to understand the
119 results?

120 Answer: [Yes]

121 Justification: Training details for the HMM and neural network surrogate are described in
122 Section 4.

123 **7. Experiment Statistical Significance**

124 Question: Does the paper report error bars suitably and correctly defined?

125 Answer: [Yes]

126 Justification: Confidence intervals for the thermal predictions are included in the results
127 figures.

128 **8. Experiments Compute Resources**

129 Question: Does the paper provide sufficient information on the computer resources?

- 130 Answer: [Yes]
131 Justification: The type of compute workers (GPU specs) and training time are specified in
132 the supplementary material.
- 133 **9. Code Of Ethics**
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147 Justification: The models developed are specific to circuit design and do not pose high risks
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156 Justification: The new dataset of micro-LED thermal simulations is documented in the
157 appendix.
- 158 **14. Crowdsourcing and Research with Human Subjects**
159 Question: For crowdsourcing experiments and research with human subjects, does the paper
160 include full instructions?
161 Answer: [N/A]
162 Justification: No human subjects were involved in this research.
- 163 **15. Institutional Review Board (IRB) Approvals**
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165 Answer: [N/A]
166 Justification: Not applicable as no human subjects were involved.